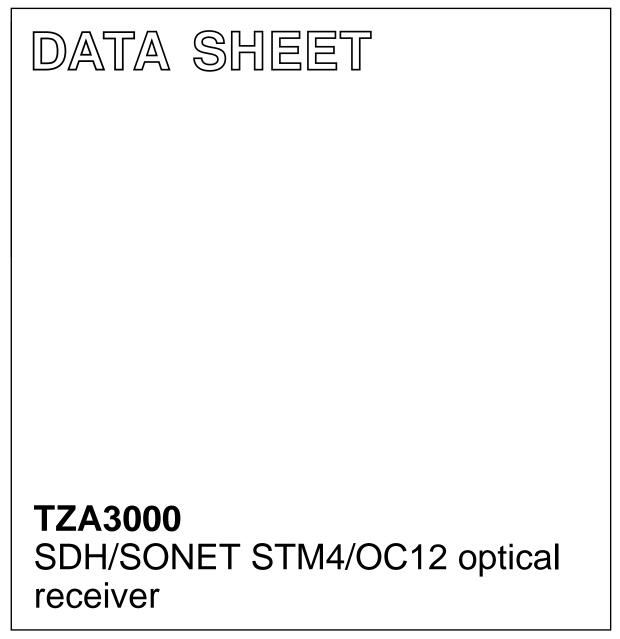


## INTEGRATED CIRCUITS



Objective specification File under Integrated Circuits, IC19





### TZA3000

#### FEATURES

- Low equivalent input noise, typically 3.5 pA/\/Hz
- Wide dynamic range, typically 1  $\mu$ A to 1.5 mA
- On-chip low-pass filter. The bandwidth can be varied between 370 and 600 MHz using an external resistor. Default value is 470 MHz.
- Differential transimpedance of 1.8  $M\Omega$
- On-chip AGC (Automatic Gain Control)
- PECL (Positive Emitter-Coupled Logic) or CML (Current-Mode Logic) compatible data outputs
- LOS (Loss-Of-Signal) detection
- LOS threshold level can be adjusted using a single external resistor
- On-chip DC offset compensation
- Single supply voltage from 3.0 to 5.5 V
- Bias voltage for PIN diode.

#### **ORDERING INFORMATION**

#### APPLICATIONS

- Digital fibre optic receiver in short, medium and long haul optical telecommunications transmission systems or in high speed data networks
- Wideband RF gain block.

#### DESCRIPTION

The TZA3000 optical receiver is a low-noise transimpedance amplifier with AGC plus a limiting amplifier designed to be used in SDH/SONET fibre optic links. The TZA3000 amplifies the current generated by a photo detector (PIN diode or avalanche photodiode) and converts it to a differential output voltage.

TYPE		PACKAGE			
NUMBER	NAME	NAME DESCRIPTION VER			
TZA3000HL	LQFP32	plastic low profile quad flat package; 32 leads; body $5 \times 5 \times 1.4$ mm	SOT401-1		
TZA3000U	naked die	naked die die in waffle pack carriers; die dimensions 1.58 × 1.58 mm –			

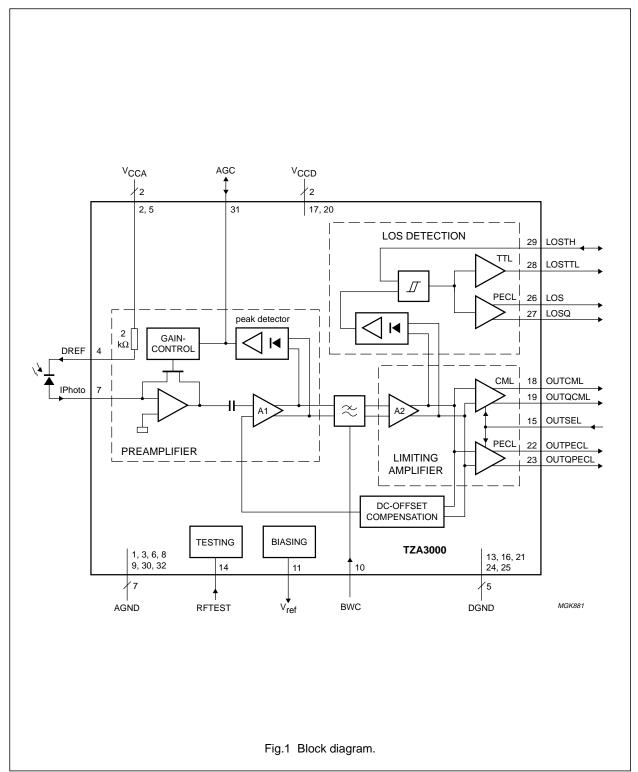


Objective specification

TZA3000

## SDH/SONET STM4/OC12 optical receiver

#### **BLOCK DIAGRAM**





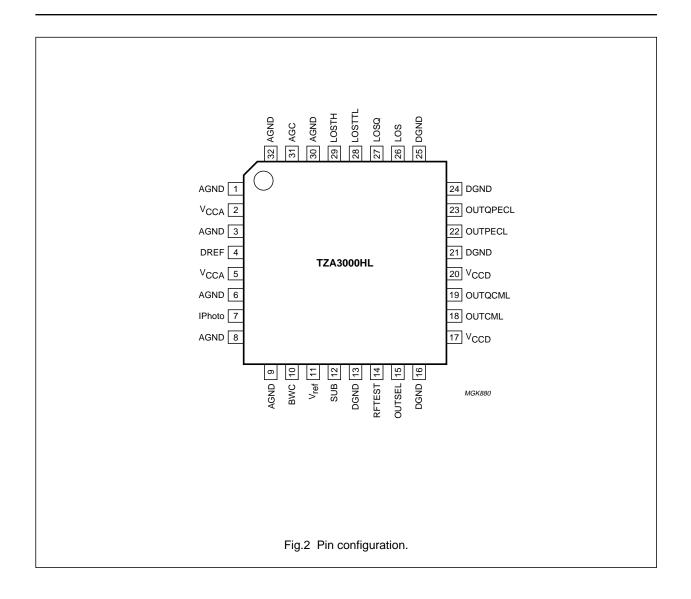
## TZA3000

#### PINNING

SYMBOL	PIN	TYPE	DESCRIPTION		
AGND	1	ground	analog ground		
V <sub>CCA</sub>	2	supply	analog supply voltage		
AGND	3	ground	analog ground		
DREF	4	analog output	bias voltage for PIN diode (V <sub>CCA</sub> ); cathode should be connected to this pin		
V <sub>CCA</sub>	5	supply	nalog supply voltage		
AGND	6	ground	analog ground		
IPhoto	7	analog input	urrent input; connect the anode of PIN diode to this pin; DC bias level is 00 mV, one diode voltage above ground		
AGND	8	ground	analog ground		
AGND	9	ground	analog ground		
BWC	10	analog input	bandwidth control pin; default bandwidth is 470 MHz; a resistor should be connected between $V_{ref}$ (pin 11) and BWC (pin 10) to decrease bandwidth, or between BWC (pin 10) and AGND to increase bandwidth		
V <sub>ref</sub>	11	analog output	band gap reference voltage; nominal value approximately 1.2 V		
SUB	12	substrate	substrate pin; to be connected to AGND		
DGND	13	ground	digital ground		
RFTEST	14	analog input	test pin; not used in application; not connected		
OUTSEL	15	CMOS input	output select pin; when OUTSEL is HIGH, CML data outputs are active and PECL data outputs are disabled; OUTSEL is pulled LOW if left unconnected, PECL data outputs will then be active and CML data outputs disabled		
DGND	16	ground	digital ground		
V <sub>CCD</sub>	17	supply	digital supply voltage		
OUTCML	18	CML output	CML data output; OUTCML goes HIGH when current flows into IPhoto (pin 7)		
OUTQCML	19	CML output	CML compliment of OUTCML (pin 18)		
V <sub>CCD</sub>	20	supply	digital supply voltage		
DGND	21	ground	digital ground		
OUTPECL	22	PECL output	PECL data output; OUTPECL goes HIGH when current flows into IPhoto (pin 7)		
OUTQPECL	23	PECL output	PECL compliment of OUTPECL (pin 22)		
DGND	24	ground	digital ground		
DGND	25	ground	digital ground		
LOS	26	PECL output	PECL-compatible LOS detection pin; LOS output is HIGH when the input signal is below the user programmable threshold level		
LOSQ	27	PECL output	PECL compliment of LOS		
LOSTTL	28	TTL output	CMOS-compatible LOS detection pin; the LOSTTL output is HIGH when the input signal is below the user programmable threshold level		
LOSTH	29	analog I/O	pin for setting input threshold level; nominal DC voltage is $V_{CCA} - 1.5$ V; threshold level set by connecting an external resistor between LOSTH and $V_{CCA}$ or by forcing a current into LOSTH; default value for this resistor is 86 k $\Omega$		
AGND	30	ground	analog ground		
AGC	31	analog I/O	AGC monitor voltage; the internal AGC circuit can be disabled by applying an external voltage to this pin		
AGND	32	ground	analog ground		



### TZA3000





### TZA3000

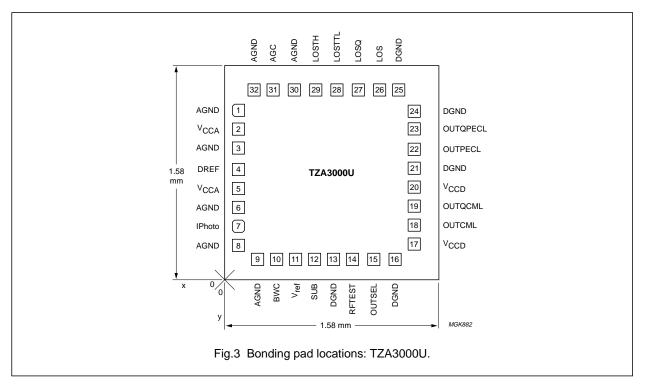
SYMBOL	PAD	COORDINATES <sup>(1)</sup>		
SYMBOL	PAD	x	У	
AGND	1	102	1251	
V <sub>CCA</sub>	2	102	1 1 1 1	
AGND	3	102	971	
DREF	4	102	814	
V <sub>CCA</sub>	5	102	674	
AGND	6	102	534	
IPhoto	7	102	395	
AGND	8	102	254	
AGND	9	243	105	
BWC	10	383	105	
V <sub>ref</sub>	11	523	105	
SUB	12	663	105	
DGND	13	803	105	
RFTEST	14	943	105	
OUTSEL	15	1 100	105	
DGND	16	1257	105	
V <sub>CCD</sub>	17	1 398	263	
OUTCML	18	1 398	403	

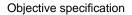
#### CHIP DIMENSIONS AND BONDING PAD LOCATIONS

CYMPOL	DAD	COORDINATES <sup>(1)</sup>		
SYMBOL	PAD	x	У	
OUTQCML	19	1 398	543	
V <sub>CCD</sub>	20	1 398	683	
DGND	21	1 398	823	
OUTPECL	22	1 398	963	
OUTQPECL	23	1 398	1103	
DGND	24	1 398	1243	
DGND	25	1283	1400	
LOS	26	1143	1400	
LOSQ	27	986	1400	
LOSTTL	28	829	1400	
LOSTH	29	671	1400	
AGND	30	514	1400	
AGC	31	357	1400	
AGND	32	217	1400	

#### Note

1. All coordinates are referenced, in  $\mu$ m, to the bottom left-hand corner of the die.





TZA3000

### SDH/SONET STM4/OC12 optical receiver

#### FUNCTIONAL DESCRIPTION

The TZA3000 contains five functional blocks:

- Preamplifier input stage
- · Low-pass filter
- · Limiting amplifier stage
- Offset compensation loop
- Loss-of-signal detection unit.

#### Preamplifier

The preamplifier provides low-noise amplification of the current generated by a photodiode connected to the IPhoto pin.

A differential amplifier converts the output of the preamplifier to a differential voltage. An AGC loop increases the dynamic range of the receiver by reducing the feedback resistance of the preamplifier. The AGC loop hold capacitor is integrated on-chip, so an external capacitor is not needed for AGC. The AGC voltage can be monitored at pin 31. This pin can be left unconnected for normal operation. It can also be used to force an external AGC voltage. If pin 31 (AGC) is connected to AGND, the internal AGC loop is disabled and the receiver gain is at a maximum. In this case, the maximum input current is about 50  $\mu$ A.

#### Low-pass filter

A low-pass filter controls the bandwidth of the receiver, which can be varied between 300 and 600 MHz. The bandwidth is set to 470 MHz by default. It can be decreased by connecting a resistor between BWC (pin 10) and  $V_{ref}$  (pin 11) or increased by connecting a resistor between BWC and AGND.

#### Limiting amplifier

A limiting amplifier boosts the signal up to PECL levels. The output can be either CML or PECL compatible, selected by means of pin OUTSEL. When OUTSEL is HIGH, CML data outputs are active and PECL data outputs are disabled. If OUTSEL is left unconnected, it is pulled LOW and PECL data outputs are active while CML data outputs are disabled.

#### Offset cancellation loop

A control loop connected between the limiting amplifier output and the differential amplifier input cancels the DC offset. The loop bandwidth is fixed internally at 30 kHz.

#### Loss-of-signal detection (LOS)

The LOS section detects an input signal level below a fixed threshold. The threshold is determined by the current through pin LOSTH. If this current is increased, the threshold level will rise. An external resistor between LOSTH and V<sub>CCA</sub> can be used, or a current can be forced into LOSTH. The default value for the external resistor is 86 k $\Omega$ . In this case, the current through LOSTH will be approximately 17.4 µA since the voltage at pin LOSTH is regulated at 1.5 V below the supply voltage. This threshold corresponds to an input current of 0.96 µA. The ratio of LOSTH current to input current is thus approximately 18:1. When the input signal level falls below this threshold, the LOS (PECL compatible) and LOSTTL (TTL compatible) outputs go HIGH. The hysteresis is fixed internally at 3 dB. Response time is typically less than 20 µs.



### TZA3000

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
Vcc	supply voltage	-0.5	+6	V
V <sub>n</sub>	DC voltage			
	pin 7: IPhoto	-0.5	+1	V
	pin 14: RFTEST	-0.5	V <sub>CC</sub> + 0.5	V
	pins 22, 23, 26 and 27: OUTPECL, OUTQPECL, LOS and LOSQ	$V_{CC} - 2$	V <sub>CC</sub> + 0.5	V
	pins 18 and 19: OUTCML and OUTQCML	$V_{CC} - 2$	V <sub>CC</sub> + 0.5	V
	pin 29: LOSTH	-0.5	V <sub>CC</sub> + 0.5	V
	pin 10: BWC	-0.5	+3.2	V
	pin 31: AGC	-0.5	V <sub>CC</sub> + 0.5	V
	pin 11: V <sub>ref</sub>	-0.5	+3.2	V
	pin 4: DREF	-0.5	V <sub>CC</sub> + 0.5	V
	pin 15: OUTSEL	-0.5	V <sub>CC</sub> + 0.5	V
	pin 28: LOSTTL	-0.5	V <sub>CC</sub> + 0.5	V
I <sub>n</sub>	DC current			
	pin 7: IPhoto	-1	+2.5	mA
	pin 14: RFTEST	-2	+2	mA
	pins 22, 23, 26 and 27: OUTPECL, OUTQPECL, LOS and LOSQ	-25	+10	mA
	pins 18,19: OUTCML and OUTQCML	–15	+15	mA
	pin 29: LOSTH	-2	+2	mA
	pin 10: BWC	-1	+1	mA
	pin 31: AGC	-0.2	+0.2	mA
	pin 11: V <sub>ref</sub>	-2	+2.5	mA
	pin 4: DREF	-2.5	+2.5	mA
	pin 15: OUTSEL	-0.5	+0.5	mA
	pin 28: LOSTTL	-16	+16	mA
P <sub>tot</sub>	total power dissipation		600	mW
T <sub>stg</sub>	storage temperature		+150	°C
Tj	junction temperature	-	150	°C
T <sub>amb</sub>	ambient temperature	-40	+85	°C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th(j-s)</sub>	thermal resistance from junction to solder point	tbf	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	tbf	K/W



TZA3000

#### CHARACTERISTICS

For typical values  $T_{amb} = 25$  °C and  $V_{CC} = 5$  V; minimum and maximum values are valid over the entire ambient temperature range and process spread.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>CC</sub>	supply voltage		3	5	5.5	V
I <sub>CCD</sub>	digital supply current	note 1	13	20	28	mA
		note 2	-	47	_	mA
		note 3	11	17	24	mA
I <sub>CCA</sub>	analog supply current		24	36	51	mA
P <sub>tot</sub>	total power dissipation		-	-	525	mW
Tj	junction temperature		-40	-	+110	°C
T <sub>amb</sub>	ambient temperature		-40	+25	+85	°C
R <sub>tr</sub>	small-signal transresistance of the receiver	measured differentially at PECL outputs	-	1800	-	kΩ
		measured differentially at CML outputs	-	1100	-	kΩ
f <sub>-3dB(h)</sub>	high frequency –3dB point	pin BWC left unconnected; note 4	-	470	-	MHz
f_3dB(I)	low frequency –3dB point		20	30	40	kHz
I <sub>i(IPhoto)(p-p)</sub>	input current on pin IPhoto	$V_{CC} = 5 V$	-400	+4	+1500	μA
	(peak-to-peak value)	V <sub>CC</sub> = 3.3 V	-400	+4	+500	μA
V <sub>bias</sub> (IPhoto)	input bias voltage on pin IPhoto		720	800	970	mV
I <sub>n(tot)</sub>	total integrated RMS noise	C <sub>i</sub> = 1.2 pF; note 5				
	current over bandwidth	∆f = 311 MHz	-	55	_	nA
	(referenced to input)	∆f = 450 MHz	-	80	-	nA
		∆f = 622 MHz	-	120	_	nA
PSRR	power supply rejection ratio at $V_{CC}$	measured differentially; note 6				
		f = 100 kHz to 10 MHz	-	1	2	μA/V
		f = 10 MHz to 100 MHz	-	2	5	μA/V
		f = 100 MHz to 1 GHz	-	5	100	μA/V
$\Delta R_{tr} / \Delta t$	AGC loop constant		-	1	-	dB/ms
PECL outp	outs: OUTPECL and OUTQPE	CL			-	
V <sub>OL</sub>	LOW-level output voltage	50 $\Omega$ to V <sub>CC</sub> – 2 V	V <sub>CC</sub> – 1100	_	V <sub>CC</sub> - 900	mV
V <sub>OH</sub>	HIGH-level output voltage	$50 \Omega$ to V <sub>CC</sub> – 2 V	V <sub>CC</sub> – 1840	-	V <sub>CC</sub> – 1620	mV
V <sub>OO</sub>	differential output offset voltage		-10	-	+10	mV
t <sub>r</sub>	rise time	20% to 80%	-	200	300	ps
t <sub>f</sub>	fall time	80% to 20%	-	140	250	ps



#### Objective specification

### SDH/SONET STM4/OC12 optical receiver

### TZA3000

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	
PECL outp	outs: LOS and LOSQ			I	1	1
V <sub>OL</sub>	LOW-level output voltage	50 $\Omega$ to V <sub>CC</sub> – 2 V	V <sub>CC</sub> – 1100	-	V <sub>CC</sub> - 900	mV
V <sub>OH</sub>	HIGH-level output voltage	50 $\Omega$ to V <sub>CC</sub> – 2 V	V <sub>CC</sub> – 1840	-	V <sub>CC</sub> – 1620	mV
V <sub>OO</sub>	differential output offset voltage		-10	-	+10	mV
t <sub>r</sub>	rise time	20% to 80%	_	-	600	ns
t <sub>f</sub>	fall time	80% to 20%	_	-	200	ns
CML outpu	Its: OUTCML and OUTQCML		·			
Vo	single ended output voltage	50 $\Omega$ to V <sub>CC</sub>	V <sub>CC</sub> – 260	-	V <sub>CC</sub>	mV
V <sub>o(se)(p-p)</sub>	single-ended output voltage (peak-to-peak value)	50 $\Omega$ to V_{CC}	150	200	260	mV
V <sub>OO</sub>	differential output offset voltage	50 $\Omega$ to V_{CC}	-10	-	+10	mV
R <sub>o</sub>	single ended output resistance		80	100	120	Ω
t <sub>r</sub>	rise time	20% to 80%; 50 Ω, 1 pF load	-	92	-	ps
t <sub>f</sub>	fall time	80% to 20%; 50 Ω, 1 pF load	-	62	-	ps
CMOS inp	ut: OUTSEL		·			
V <sub>IL</sub>	LOW-level input voltage		-	0.4	0.8	V
V <sub>IH</sub>	HIGH-level input voltage		V <sub>CC</sub> – 1	$V_{CC} - 0.5$	-	V
CMOS out	put: LOSTTL					•
V <sub>OL</sub>	LOW-level output voltage		0	-	0.2	V
V <sub>OH</sub>	HIGH-level output voltage		V <sub>CC</sub> – 0.2	_	V <sub>CC</sub>	V

#### Notes

- 1. OUTPECL, OUTQPECL, OUTCML, OUTQCML, LOS and LOSQ outputs are left unconnected. OUTPECL and OUTQPECL outputs are active.
- OUTPECL and OUTQPECL outputs are terminated with 50 Ω to V<sub>T</sub>. V<sub>T</sub> is an external termination voltage for PECL outputs and is 2 V below the supply voltage. OUTCML, OUTQCML, LOS and LOSQ outputs are left unconnected
- 3. OUTCML and OUTQCML outputs are terminated with 50  $\Omega$  to V<sub>CCD</sub>; CML outputs are active. OUTPECL, OUTQPECL, LOS and LOSQ outputs are left unconnected
- 4. The bandwidth is set to 470 MHz by default. It can be varied between 300 and 600 MHz by adjusting the voltage at pin BWC.
- 5. All  $I_{n(tot)}$  measurements were made with an input capacitance of  $C_i = 1.2 \text{ pF}$ . This was comprised of 0.7 pF for the photodiode itself, with 0.3 pF allowed for the PCB layout and 0.2 pF intrinsic to the package.
- 6. PSRR is defined as the ratio of the equivalent current change at the input ( $\Delta I_{IPhoto}$ ) to a change in supply voltage:

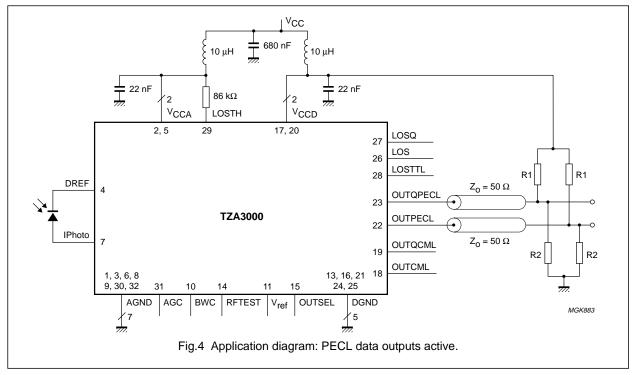
$$\mathsf{PSRR} = \frac{\Delta \mathsf{I}_{\mathsf{IPhoto}}}{\Delta \mathsf{V}_{\mathsf{CC}}}$$

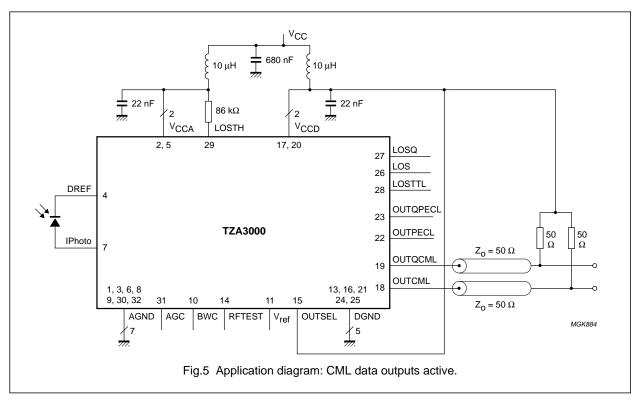
For example, a 1 mV disturbance on V<sub>CC</sub> at 10 MHz will typically generate the equivalent of 2 nA extra photodiode current.



TZA3000

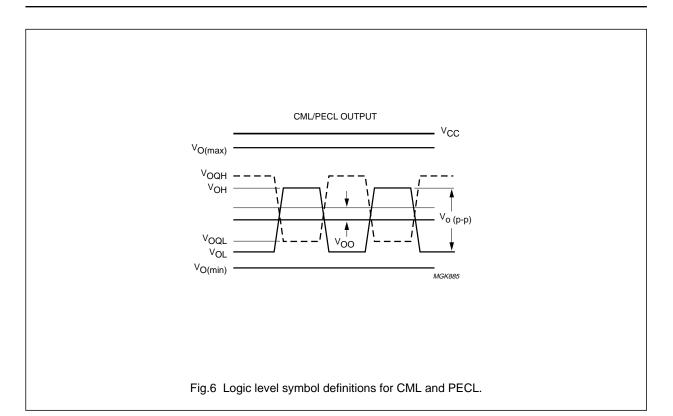
#### **APPLICATION INFORMATION**

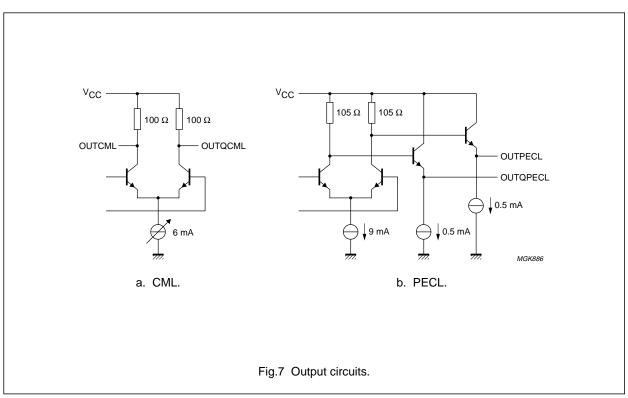






### TZA3000



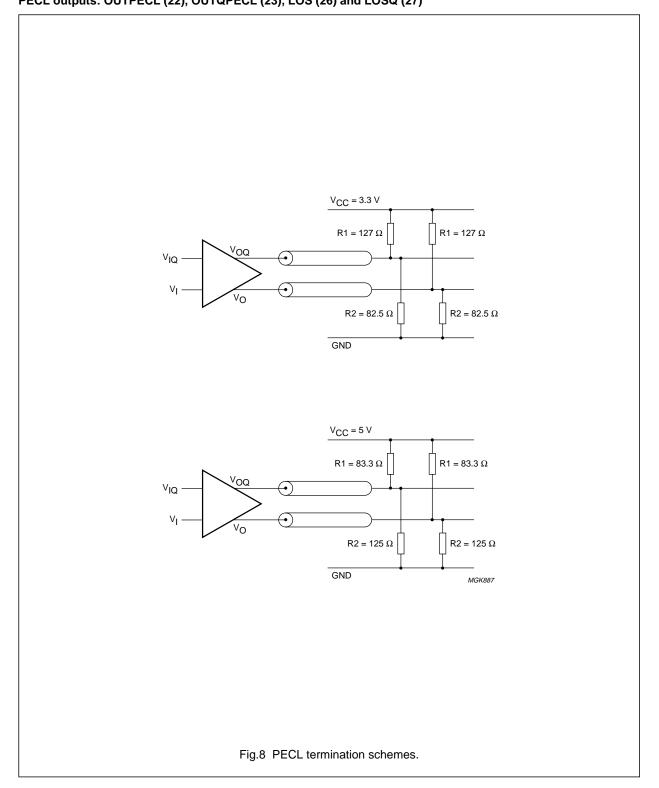




TZA3000

### SDH/SONET STM4/OC12 optical receiver

# PECL outputs: OUTPECL (22), OUTQPECL (23), LOS (26) and LOSQ (27)





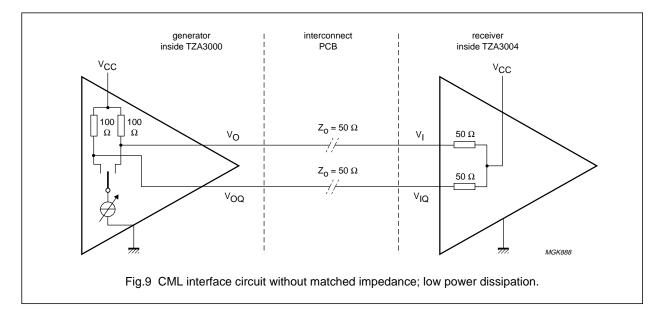
### TZA3000

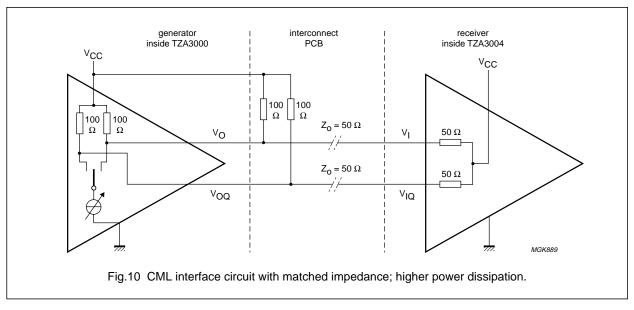
#### CML outputs: OUTCML (18) and OUTQCML (19)

The output impedance of the CML output driver is 100  $\Omega$  (see Figs 7 and 9), which doesn't match the characteristic impedance of the strip line. While this means that the reflections of some incident edges will arrive at the driver output on the PCB, this value was selected to reduce power dissipation inside the IC. The parallel combination of 100  $\Omega$  and 50  $\Omega$  (33  $\Omega$ ) will generate a signal swing of 200 mV peak-to-peak (single sided) with a tail current of 6 mA. If the output impedance was 50  $\Omega$  rather than

100  $\Omega$ , an 8 mA tail current would be needed to generate the same voltage swing. This would increase power dissipation by 33%.

If necessary, the output impedance of the generator can be matched to the line impedance by connecting an external 100  $\Omega$  resistor in parallel with the output as shown in Fig.10. The magnitude of the output voltage swing will not change due to adaptive regulation. However, power dissipation will increase by 33%.





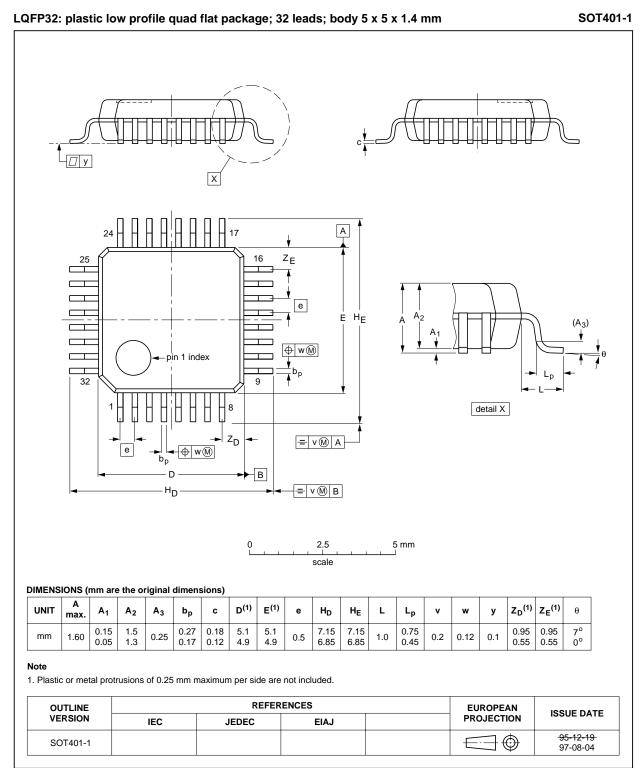


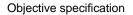
#### Objective specification

### SDH/SONET STM4/OC12 optical receiver

### TZA3000

#### PACKAGE OUTLINE





### TZA3000

#### SOLDERING

#### Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

#### **Reflow soldering**

Reflow soldering techniques are suitable for all LQFP packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

#### Wave soldering

Wave soldering is **not** recommended for LQFP packages. This is because of the likelihood of solder bridging due to closely-spaced leads and the possibility of incomplete solder penetration in multi-lead devices. If wave soldering cannot be avoided, the following conditions must be observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The footprint must be at an angle of 45° to the board direction and must incorporate solder thieves downstream and at the side corners.

Even with these conditions, do not consider wave soldering LQFP packages LQFP48 (SOT313-2), LQFP64 (SOT314-2) or LQFP80 (SOT315-1).

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

#### **Repairing soldered joints**

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.



### TZA3000

#### DEFINITIONS

Data sheet status				
Dbjective specification This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
more of the limiting values of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.			
Application information				

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.



NOTES

Objective specification

TZA3000



NOTES

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Objective specification

TZA3000



# Philips Semiconductors – a worldwide company

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